EVVOSEMI®

THINK CHANGE DO

ESD TVS MOS LDO Diode Sensor DC-DC

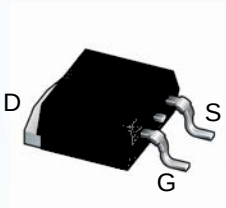
Product Specification

Domestic Part Number	IRFR3410
Overseas Part Number	IRFR3410
Equivalent Part Number	IRFR3410

N-Channel Enhancement Mode MOSFET

Description

The IRFR3410 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

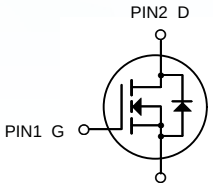


TO-252-2L

General Features

V_{DS} = 100V I_D = 30A

$R_{DS(ON)}$ < 48mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRFR3410	TO-252-2L	EVVO MOSFET	2500

Absolute Maximum Ratings T_C=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	30	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	13	A
I_{DM}	Pulsed Drain Current[2]	80	A
EAS	Single Pulse Avalanche Energy[3]	30	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	42	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	3.6	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=100V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=10A	-	37	48	mΩ
		V_{GS}=4.5V, I_D=6A	-	39	55	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	1964	-	pF
C_{oss}	Output Capacitance		-	90	-	pF
C_{rss}	Reverse Transfer Capacitance		-	74	-	pF
Q_g	Total Gate Charge	V_{DS}=80V, I_D=20A, V_{GS}=4.5V	-	20	-	nC
Q_{gs}	Gate-Source Charge		-	3.1	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	14	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=80V, I_D=20A, R_G=3.1Ω, V_{GS}=4.5V	-	11	-	ns
t_r	Turn-on Rise Time		-	91	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	40	-	ns
t_f	Turn-off Fall Time		-	71	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	27	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=100A/μs	-	64	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	152	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25℃,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25Ω,I_{AS}= 11A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

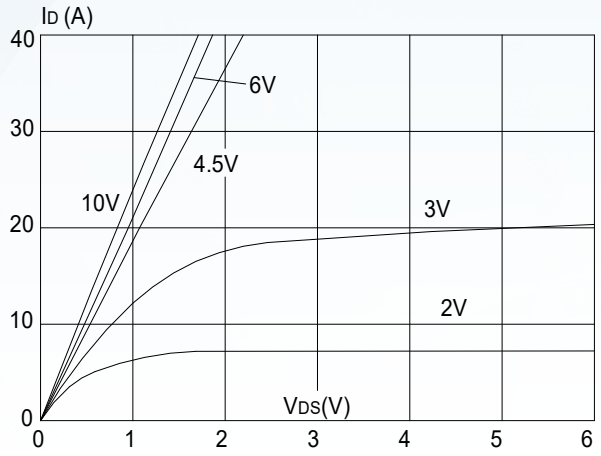


Figure 2: Typical Transfer Characteristics

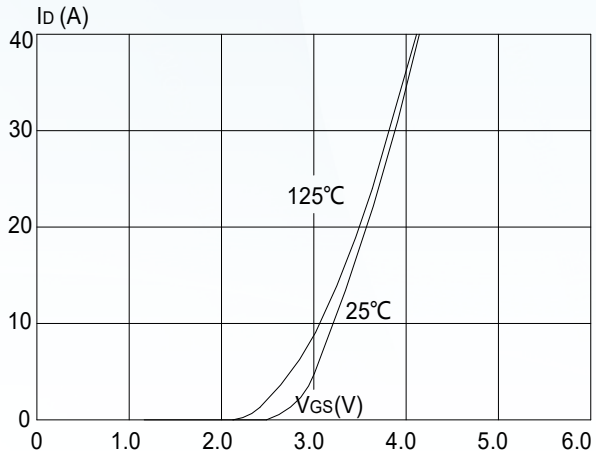


Figure 3: On-resistance vs. Drain Current

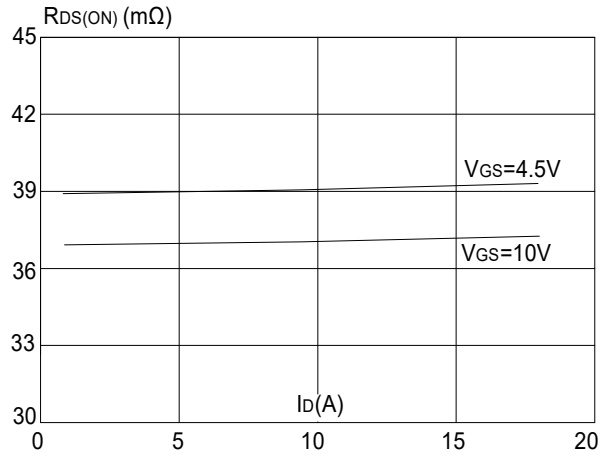


Figure 4: Body Diode Characteristics

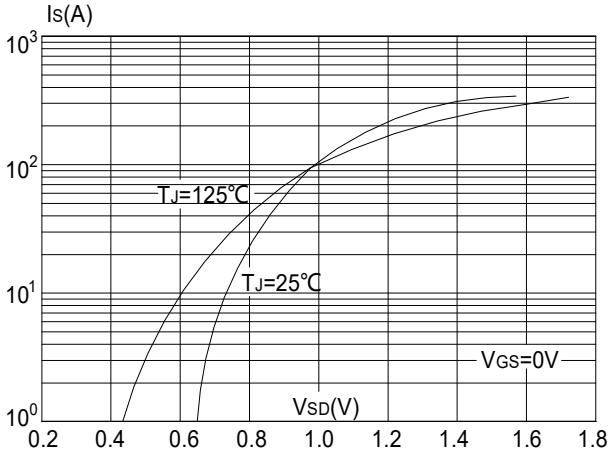


Figure 5: Gate Charge Characteristics

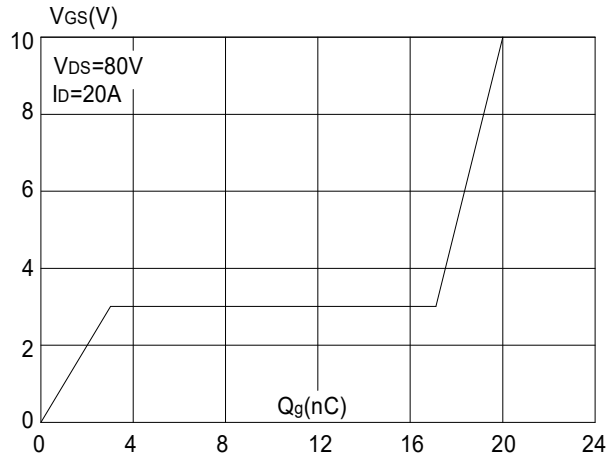


Figure 6: Capacitance Characteristics

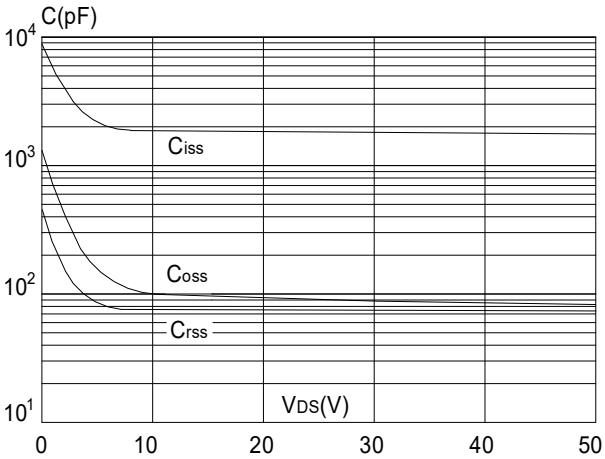


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

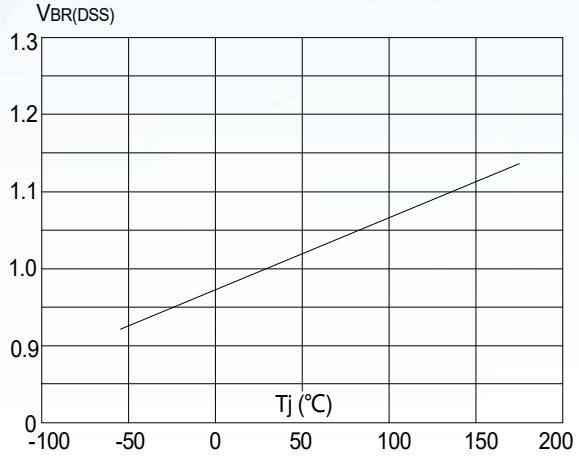


Figure 8: Normalized on Resistance vs. Junction Temperature

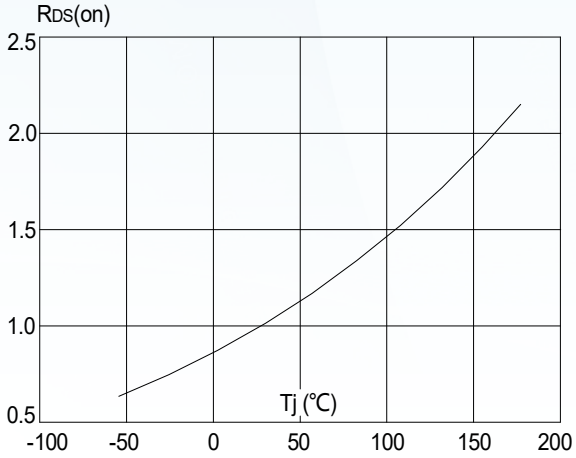


Figure 9: Maximum Safe Operating Area

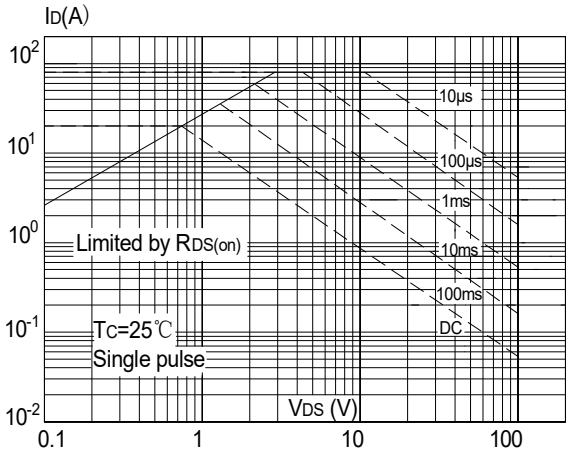


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

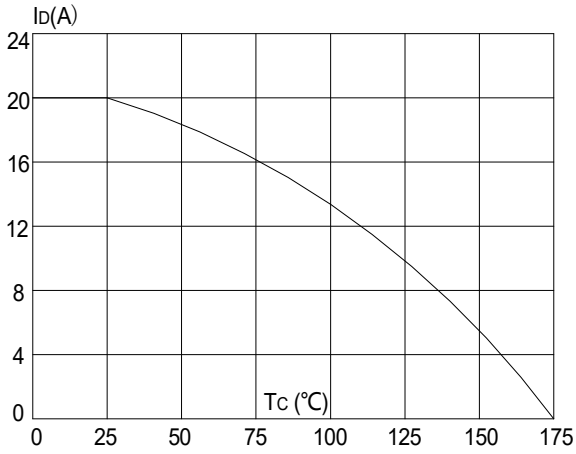
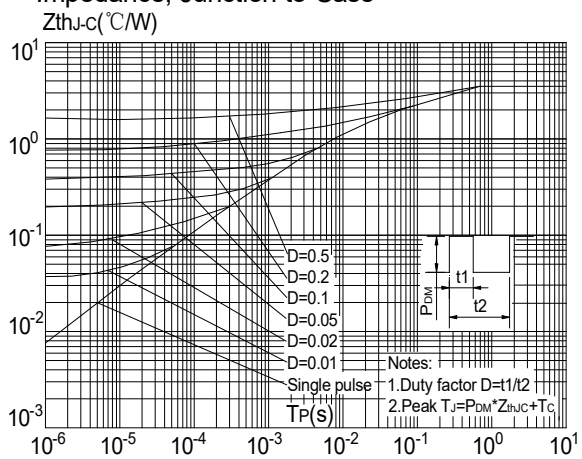
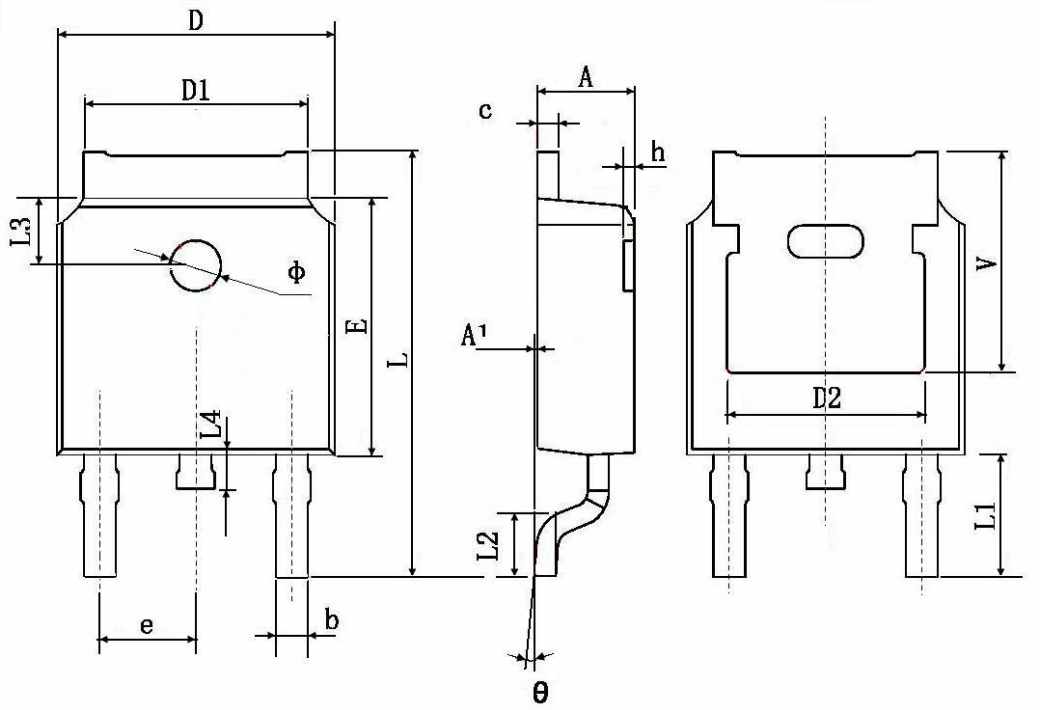


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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